

Yuanpeng Wu

List of Publications by Year in descending order

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24
papers

848
citations

430754

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610775

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24
all docs

24
docs citations

24
times ranked

783
citing authors

#	ARTICLE	IF	CITATIONS
1	N-polar InGaN nanowires: breaking the efficiency bottleneck of nano and micro LEDs. <i>Photonics Research</i> , 2022, 10, 587.	3.4	31
2	Scalable Synthesis of Monolayer Hexagonal Boron Nitride on Graphene with Giant Bandgap Renormalization. <i>Advanced Materials</i> , 2022, 34, e2201387.	11.1	22
3	Interfacial Modulated Lattice-Polarity-Controlled Epitaxy of III-Nitride Heterostructures on Si(111). <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 15747-15755.	4.0	13
4	III-nitride nanostructures: Emerging applications for Micro-LEDs, ultraviolet photonics, quantum optoelectronics, and artificial photosynthesis. <i>Progress in Quantum Electronics</i> , 2022, 85, 100401.	3.5	26
5	Oxygen defect dominated photoluminescence emission of $\text{ScAl}_{1-x}\text{N}$ grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	22
6	N-polar ScAlN and HEMTs grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	27
7	Bidirectional photocurrent in p^{n} heterojunction nanowires. <i>Nature Electronics</i> , 2021, 4, 645-652.	13.1	129
8	Monolithic integration of multicolor InGaN LEDs with uniform luminescence emission. <i>Optics Express</i> , 2021, 29, 32826.	1.7	7
9	High efficiency InGaN nanowire tunnel junction green micro-LEDs. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	16
10	Monolayer GaN excitonic deep ultraviolet light emitting diodes. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	39
11	Micrometer scale InGaN green light emitting diodes with ultra-stable operation. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	21
12	Controlling Defect Formation of Nanoscale AlN: Toward Efficient Current Conduction of Ultrawide-Bandgap Semiconductors. <i>Advanced Electronic Materials</i> , 2020, 6, 2000337.	2.6	19
13	Hyperspectral absorption of semiconductor monolayer crystals. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	4
14	Deep ultraviolet monolayer GaN/AlN disk-in-nanowire array photodiode on silicon. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	18
15	Deep Ultraviolet Luminescence Due to Extreme Confinement in Monolayer GaN/Al(GaN) Nanowire and Planar Heterostructures. <i>Nano Letters</i> , 2019, 19, 7852-7858.	4.5	35
16	A quadruple-band metal-nitride nanowire artificial photosynthesis system for high efficiency photocatalytic overall solar water splitting. <i>Materials Horizons</i> , 2019, 6, 1454-1462.	6.4	38
17	An $\text{In}_{0.42}\text{Ga}_{0.58}\text{N}$ tunnel junction nanowire photocathode monolithically integrated on a nonplanar Si wafer. <i>Nano Energy</i> , 2019, 57, 405-413.	8.2	38
18	Molecular beam epitaxy and characterization of AlGaN nanowire ultraviolet light emitting diodes on Al coated Si (001) substrate. <i>Journal of Crystal Growth</i> , 2019, 507, 65-69.	0.7	26

#	ARTICLE	IF	CITATIONS
19	Improving performance of Si/CdS micro-/nanoribbon p-n heterojunction light emitting diodes by trenched structure. AIP Advances, 2018, 8, 055231.	0.6	3
20	Wafer-scale synthesis of monolayer WSe ₂ : A multi-functional photocatalyst for efficient overall pure water splitting. Nano Energy, 2018, 51, 54-60.	8.2	45
21	An AlGa _N Core-Shell Tunnel Junction Nanowire Light-Emitting Diode Operating in the Ultraviolet-C Band. Nano Letters, 2017, 17, 1212-1218.	4.5	117
22	An electrically pumped 239-nm AlGa _N nanowire laser operating at room temperature. Applied Physics Letters, 2016, 109, .	1.5	71
23	Molecular beam epitaxy growth of Al-rich AlGa _N nanowires for deep ultraviolet optoelectronics. APL Materials, 2016, 4, .	2.2	62
24	High efficiency single Ag nanowire/p-GaN substrate Schottky junction-based ultraviolet light emitting diodes. Applied Physics Letters, 2015, 106, .	1.5	19